



**General Description:**

- (1) Chip Dimension  
 Chip Size= 8 mil x 10 mil (205um x 255um)  
 Chip Thickness = 100±10 μm  
 P/N Bonding Pad = 85±5 μm
- (2) Electrode:  
 P (Anode) → Au  
 N (Cathode) → Au
- (3) Structure:  
 Refer to drawing  
 SiO<sub>2</sub> Passivated surface

**Electro-optical Characteristics (Ta=RT)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V <sub>F</sub>	2.7	-	3.1	V	I <sub>F</sub> =5mA
		2.8	-	3.5	V	I <sub>F</sub> =20mA
Dominant Wavelength	λ <sub>D</sub>	450	-	470	nm	I <sub>F</sub> =5mA
		445	-	470	nm	I <sub>F</sub> =20mA
Reverse Current	I <sub>R</sub>	0	-	2	μA	V <sub>R</sub> =-5V

Luminous Intensity( I <sub>v</sub> ) mcd at I <sub>F</sub> =5mA	Dominant Wavelength(nm)												
	Range	445~447.5	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470	470~472.5	472.5~475
5~10													
10~15			*	*	*	*	*						
15~20			*	*	*	*	*	*					
20~25			*	*	*	*	*	*	*				
25~30						*	*	*	*	*			
30~35							*	*	*	*	*		
35~40										*			

Luminous Intensity( I <sub>v</sub> ) mcd at I <sub>F</sub> =20mA	Dominant Wavelength(nm)												
	Range	445~447.5	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470	470~472.5	472.5~475
30~40	*	*	*										
40~50	*	*	*	*	*								
50~60	*	*	*	*	*	*	*	*	*				
60~70		*	*	*	*	*	*	*	*				
70~80			*	*	*	*	*	*	*	*			
80~90				*	*	*	*	*	*	*			
90~100						*	*	*	*	*	*		
100~120							*	*	*	*	*		
120~140										*			

- Features:**
- 1.High Luminous Intensity
  - 2.Long Operation Life
  - 3.High Current; Pulse Operation
  - 4.Indoor/Outdoor Applications

- Notes:**
- 1. Dominant wavelength includes an error of ± 1nm
  - 2. Luminous intensity includes an error of ±10%
  - 3. Luminous intensity is measured on bare chip
  - 4.InGaN LED is sensitive to ESD